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85:1

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Title of the Thesis:	Fabrication and TCAD Simulation of TiO ₂ / ZnO Nanorods
	Electron Transport Layer based CH ₃ NH ₃ PbI ₃ Perovskite Solar Cell

Name of the Student: Deepak Kumar Jarwal

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(Deepak Kumar Jarwal)

DEDICATED TO MY BELOVED PUJYA GURUDEV

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LIST OF ABBREVIATIONS

Abbreviation	Details
PV	Photovoltaic
LED	Light Emitting Diode
РЗНТ	Poly(3-hexylthiophene)
НОМО	Highest Occupied Molecular Orbital
LUMO	Lowest Unoccupied Molecular Orbital
PEDOT	Poly(3,4-ethylenedioxythiophene)
PCE	Power Conversion Efficiency
AM	Atmospheric Mass
SPM	Scanning Probe Microscopy
AFM	Atomic Force Microscopy
STM	Scanning Tunnelling Microscopy
GaAs	Gallium Arsenide
HRSEM	High Resolution Scanning electron microscopy
EDX or EDS	Energy dispersive X-ray spectroscopy
TEM	Transmission Electron Microscopy
SAED	Selected Area Electron Diffraction
XRD	X-ray Diffraction
CIGS	Copper Indium Gallium Selenide
UV-Vis	Ultraviolet-Visible
PL	Photoluminescence
ZnO	Zinc Oxide
PET	Polyethylene Terephthalate
CdTe	Cadmium Telluride
CdS	Cadmium Sulphide
TiO ₂	Titanium dioxide

Au	Gold
Ag	Silver
Al	Aluminum
MoO ₃	Molybdenum Trioxide
RMS	Root Mean Square
ITO	Indium-Doped Tin Oxide
FTO	Fluorine Doped Tin Oxide
TCAD	Technology Computer Aided Design
EPBT	Energy Pay Back Time
PCBM	[6,6]-phenyl C ₆₁ butyric acid methyl ester
QDs	Quantum Dots
DSSCs	Dyed Sensitized Solar Cells
PSC	Perovskite Solar Cell
ETLs	Electron Transport Layers
HTLs	Hole Transport Layers
MAPbX ₃	Methyl Ammonium Lead Halides
CsPbX ₃	Caesium based Lead Halides (Cl, Br, I)
VB	Valence Band
СВ	Conduction Band
Pb	Lead
eV	Electron Volt
PTAA	Poly(triaryl amine)
TCO	Transparent Conducting Oxide
FF	Fill Factor
SRH	Shockley Read Hall
PVD	Physical Vapour Deposition
DMF	Di-Methyl Formamide
DMSO	Di-Methyl Sulfoxide

GBL	g-Butyro- Lactone
NMP	N-Methyl-2-Pyrrolidone
Al ₂ O ₃	Aluminium Oxide
PECVD	Plasma Enhanced Chemical Vapor Deposition
CBD	Chemical Bath Deposition
AC	Alternating Current
РЗНТ	Poly(3-Hexylthiophene)
CuSCN	Copper(I) thiocyanate
HTM	Hole Transport Material
ETM	Electron Transport Material
ZNRs	ZnO Nanorods
C ₆₀	Fullerenes
РСВМ	Phenyl-C61-butyric acid methyl ester
TNRs	TiO ₂ Nanorods
ZrO ₂	Zirconium dioxide
SnO ₂	Tin(IV) oxide
ALD	Atomic Layer Deposition
TiCl ₄	Titanium Tetrachloride
TTIP	Titanium Iso-propoxide
HI	Hydrogen Iodide
RPM	Rotation Per Minute
DOS	Density of State

LIST OF SYMBOLS

Symbol	Details
λ	Wavelength
heta	Diffraction angle
Т	Transmittance
Α	Absorbance
I-V	Current-voltage
CV	Capacitance-voltage
μ_e	Electron mobility
μ_h	Hole mobility
V_T	Thermal voltage
I _{SH}	Current through Shunt resistance
I_{PH}	Photo generated current
Ι	Current
I_S	Reverse Saturation Current
В	Ratio of photo-generated current to the light intensity
N_t	Defect Density
N_A	Doping concentration of Acceptor
N _D	Doping concentration of Donor
Р	Power Density
R_S	Series Resistance
E_G	Energy Band Gap
R_{SH}	Shunt Resistance
FF	Fill Factor

J_{SC}	Short Circuit Current density
η	Power Conversion Efficiency
J	Current Density
V	Voltage
X	Electron Affinity
N_C	Density of states of the Conduction Band
N_V	Density of states of the Valence Band
hv	Photon Energy
P_T	Theoretical Power
I_{sc}	Short Circuit Current
P_{in}	Incident Optical Power Density
P_{mpp}	Maximum Power Density
J_{mpp}	Maximum Current Density
V_{mpp}	Maximum Voltage
V_{OC}	Open Circuit Voltage
n	Concentration of Electrons
р	Concentration of Holes
R	Recombination Rate
G	Generation Rate
γ	Recombination Coefficient
n_i	Intrinsic Carrier Concentration
R _{SRH}	Rate of SRH combination
V	Voltage
τη	Electron Lifetime
τp	Hole Lifetime
E_C	Energy of Conduction band
E_V	Energy of valence band

- *keV* Kilo Electron Volt
- *C* Capacitance
- C_p^A Constant
- C_n^A Constant
- V Voltage
- ε_o Vacuum Permittivity
- ε_r Relative Permittivity
- $\Phi(x)$ Electrostatic Potential
- *e* Electric Charge
- *J_n* Current Density due to Electrons
- J_p Current Density due to Holes
- ρ_d Defect Charge Density

PREFACE

The worldwide increase in energy consumption has motivated scientists to explore the potential of solar energy. At present, solar energy harvesting is carried out mostly (more than 90%) by the inorganic crystalline silicon (Si) solar cells. Moreover, Si-based solar cells are now approaching their maximum theoretical limiting efficiency of ~29.43%. The latest advancements in technology and materials have led to the development of novel photosensitive materials that enabled the fabrication of low cost and highly efficient photovoltaic devices. The state of the art growth in various perovskite materials like inorganic (CsPbX₃: X=I, Cl, Br) and hybrid (ABX₃; A= organic compound, B= inorganic compound, and X= halides) have attracted huge interest among the researchers. Recently, methylammonium lead halides $(CH_3NH_3PbX_3)$ have shown highly encouraging photosensitive for photovoltaic application, which gained immense research attention since its discovery and has boosted hopes for new photovoltaic technologies.

Typically, the optical and electrical characteristics of photovoltaic devices depend upon the device design, fabrication procedures, semiconductor/active material, etc. The different synthesis and deposition techniques may be used for the tuning of the electronic and optical properties of as-grown thin films. Additionally, the lowdimension nanostructures such as nanorods or nanowires that offer large surface-tovolume ratios are mostly used for the charge transport layer in perovskite solar cells (PSC). From this perspective, the present thesis deals with the TCAD simulation, fabrication, and characterization of TiO₂/ZnO nanorods electron transport layer (ETL) based hybrid perovskite (CH₃NH₃PbI₃) solar cells. In PSCs' design, the PTAA/Spiro-OMeTAD polymer is employed as hole transport material where small molecule materials (Li-TFSI and TBP) are used as doping elements to enhance the conductivity of the hole transport layer (HTL).

The primary focus of this thesis is to explore the performance parameter of PSC by means of the synergic effects of the modified synthesis process for ETL through optimized doping in HTL. The uniformly distributed and vertically aligned TiO_2/ZnO Nanorods have been grown on FTO substrates by the hydrothermal method, whereas both HTL and absorber layers are deposited via spin-coating techniques. Later, the optical and electrical properties of TiO_2/ZnO Nanorods have been explored in detail. The thesis consists of six chapters, which are briefly outlined as follows:

Chapter-1 introduces the hybrid perovskite material's optoelectronic properties, thin-film synthesis process, and the working principle of perovskite solar cells. A brief introduction about device models and thin film characterization techniques have been discussed. Finally, a detailed literature survey, motivation, and scope of the thesis have been presented.

Chapter-2 presents TCAD simulation and fabrication of hybrid perovskite solar cells. The electrical and optical characterization has been investigated for the device structure Pd/PTAA/hybrid perovskite (CH₃NH₃PbI₃)/TiO₂ Nanorods (TNRs) grown on an FTO coated glass substrate. The TNRs layer is synthesized by a low-cost hydrothermal process and acts as the ETL, whereas the PTAA acts as the HTL. The solar cells are optimized, fabricated, and characterized for different TNRs thickness and then several device performance parameters such as short circuit current density (J_{SC}),

Preface

open-circuit voltage (V_{OC}), fill factor (*FF*), and power conversion efficiency (*PCE*) and etc. are studied. The *Solar Cell Capacitance Simulator-One Dimensional* (SCAPS-1D) is used to simulate the proposed solar cell structure and validated via our experimental results. The effects of thickness variation of ETL on the solar cell parameters have been investigated by solving the drift-diffusion model. The measurements show that the efficiency of the solar cell is decreased with the increase in ETL thickness, which is attributed to higher trap sites in the active layer and ETL. The maximum optimized efficiency of 15.04% is obtained for ETL thickness of 500 nm. On the other hand, the simulated results are in close resemblance to the experimental results, having an efficiency of 15.69%.

Chapter-3 reports the efficiency improvement of perovskite solar cells (PSCs) by solvothermal etching and TiCl₄ treatment of TNRs based ETL. The TiO₂ NRAs have been explored for the ETL due to their better direct carrier transportation over other TiO₂ nanostructures. The solvothermal etching of TiO₂ NRAs enhances the surface-to-volume ratio of the ETL, which, in turn, enhances the power conversion efficiency (PCE) of the PSCs. All the measurements have been performed at room temperature and high humid (with ~65% humidity) conditions to demonstrate the performance of the PSCs under normal environmental conditions. A noteworthy efficiency of 15.16% with an improved fill factor (FF) and short circuit current density (J_{SC}) has been reported in the proposed PSCs. The PSC performance is further improved by the TiCl₄ treatment of the solvothermally etched TiO₂ NRs as the ETL in the device.

Chapter-4 discusses the effect of the seed layer, which directly affects the growth of the ZnO Nanorods (ZNRs) and related photovoltaic parameters of the hybrid

perovskite solar cell. Four different types of ZnO seed layer samples have been synthesized using four methods, namely: ZnO drop-cast, ZnO nanoparticles (NPs), ZnO quantum dots (QDs), and ZnO solvothermal on the FTO substrate. ZnO drop-cast results in less density, tilted, and non-uniform deposition of the nanorods. But uniform coverage, high volume to the surface, and vertical direction growth of ZNRs are observed in the ZnO QD seed layer sample compared to the other three samples. Morphology and crystalline structure were analyzed with HRSEM, TEM, and XRD, whereas optical absorption, emission, and transmittance are recorded using UV-Visible, and Photoluminescence, respectively. Subsequently, the electrical characterization reveals that the optimum photovoltaic parameters are obtained on the seed layer of ZnO QD, which leads to the power conversion efficiency of 10.69% for ZnO NR based perovskite solar cell structure (FTO/ZNRS/CH₃NH₃PbI₃/PTAA/Au).

Chapter-5 presents the simulation, fabrication, and characterization of ZnO Nanorod (ZNRs) based PSCs under ambient air conditions. The proposed PSC structures use a CH₃NH₃PbI₃ hybrid perovskite-based active layer sandwiched between a ZnO Nanorods (NRs) ETL and a Spiro-OMeTAD (undoped and doped) HTL. The ZnO NRs are grown using a low-cost solvothermal process at relatively low temperature. The performance of fabricated PSCs is analyzed for both the undoped and doped (with TBP and LiTFSI) spiro-OMeTAD based HTLs. All the solar parameters, namely, short circuit current density (J_{SC}), open-circuit voltage (V_{OC}), fill factor (FF), power conversion efficiency (PCE), and external quantum efficiency (EQE), are calculated from experimentally measured current density versus voltage (J-V) and wavelength transient characteristics in ambient condition. The maximum PCE of 10.18% is obtained for the doped HTL, whereas 9.51% for undoped HTL. The

improved performance due to HTL doping is attributed to the enhanced charge transportation of the HTL. The experimental results obtained from the fabricated PSCs are also compared with the SetFosTM TCAD simulation data using the drift-diffusion model. The simulated results are observed to be well matched to the experimental data.

Chapter-6 includes the major findings of the thesis along with a brief outline for the future scope of research related to the present thesis.

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